

isc Silicon PNP Power Transistor

BD244/A/B/C

DESCRIPTION

- DC Current Gain $-h_{FE} = 30(\text{Min}) @ I_C = -0.3\text{A}$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(\text{SUS})} = -45\text{V}(\text{Min})$ - BD243; $-60\text{V}(\text{Min})$ - BD243A
 $-80\text{V}(\text{Min})$ - BD243B; $-100\text{V}(\text{Min})$ - BD243C
- Complement to Type BD243/A/B/C

APPLICATIONS

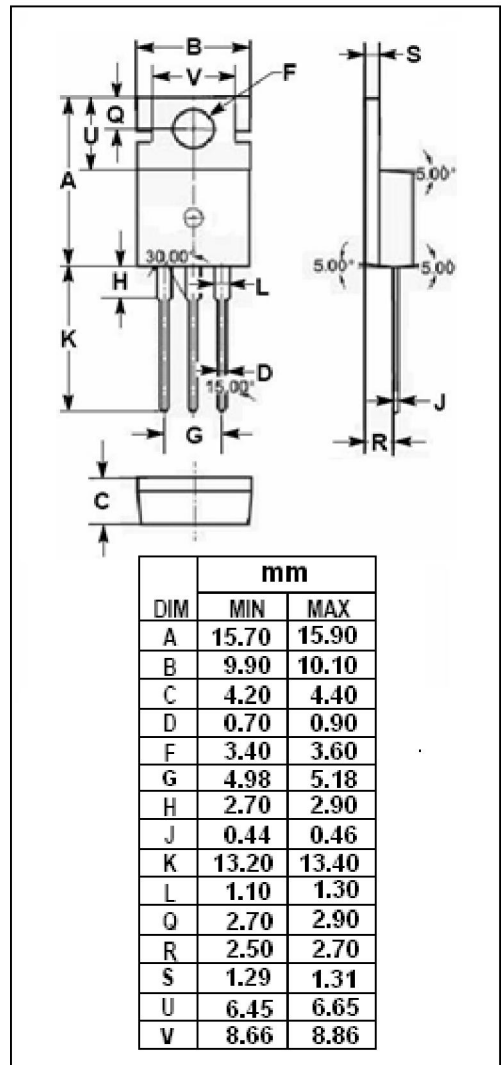
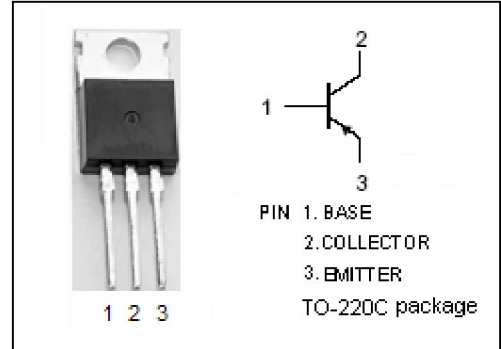
- Designed for use in general purpose power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CBO}	Collector-Base Voltage	BD244	-45	V
		BD244A	-60	
		BD244B	-80	
		BD244C	-100	
V_{CEO}	Collector-Emitter Voltage	BD244	-45	V
		BD244A	-60	
		BD244B	-80	
		BD244C	-100	
V_{EBO}	Emitter-Base Voltage	-5	V	
I_C	Collector Current-Continuous	-6.0	A	
I_{CM}	Collector Current-Peak	-10	A	
I_B	Base Current	-2.0	A	
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	65	W	
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.92	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

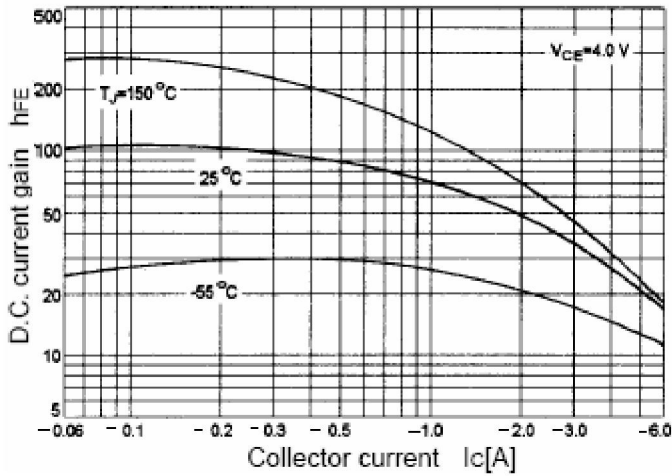
 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	MAX	UNIT
$V_{CE(SUS)}$	Collector-Emitter Sustaining Voltage	BD244	$I_C = -30\text{mA}; I_B = 0$	-45		V
		BD244A		-60		
		BD244B		-80		
		BD244C		-100		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		$I_C = -6\text{A}; I_B = -1\text{A}$		-1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage		$I_C = -6\text{A}; V_{CE} = -4\text{V}$		-2.0	V
I_{CES}	Collector Cutoff Current	BD244	$V_{CE} = -45\text{V}; V_{BE} = 0$		-0.4	mA
		BD244A	$V_{CE} = -60\text{V}; V_{BE} = 0$			
		BD244B	$V_{CE} = -80\text{V}; V_{BE} = 0$			
		BD244C	$V_{CE} = -100\text{V}; V_{BE} = 0$			
I_{CEO}	Collector Cutoff Current	BD244/A	$V_{CE} = -30\text{V}; I_B = 0$		-0.7	mA
		BD244B/C	$V_{CE} = -60\text{V}; I_B = 0$			
I_{EBO}	Emitter Cutoff Current		$V_{EB} = -5\text{V}; I_C = 0$		-1.0	mA
h_{FE-1}	DC Current Gain		$I_C = -0.3\text{A}; V_{CE} = -4\text{V}$	30		
h_{FE-2}	DC Current Gain		$I_C = -3\text{A}; V_{CE} = -4\text{V}$	15		
f_T	Current-Gain—Bandwidth Product		$I_C = -0.5\text{A}; V_{CE} = -10\text{V}, f_{test} = 1.0\text{MHz}$	3.0		MHz

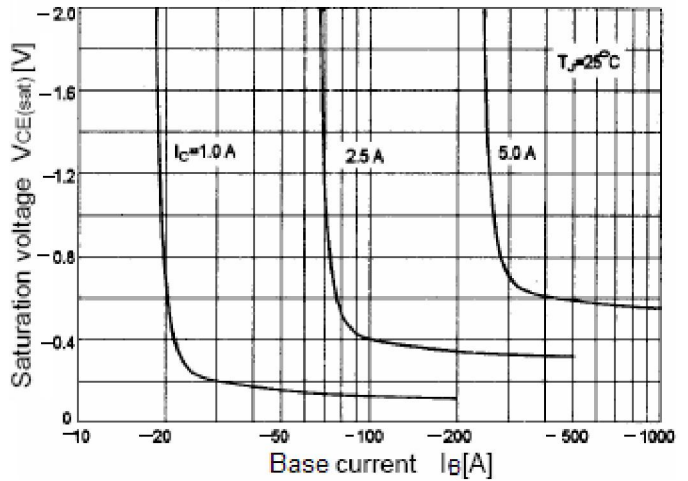
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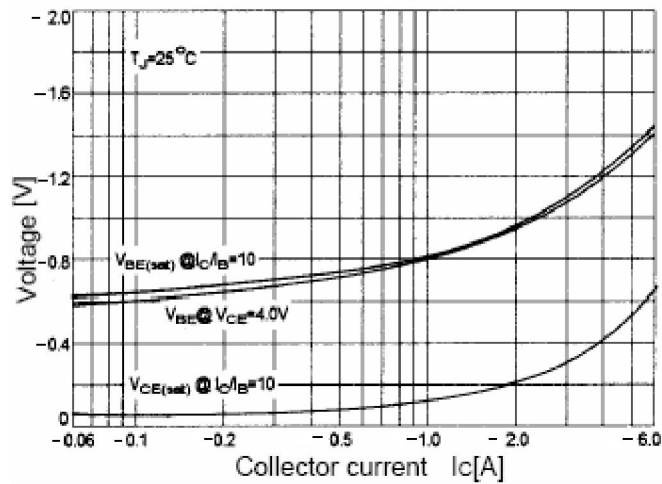
$h_{FE}-I_C$ Characteristics



$V_{CE(sat)}-I_B$ Characteristics



"On" Voltages



Safe Operating Area

